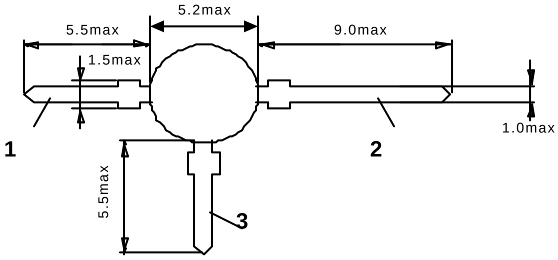
BFR96

N-P-N bipolar silicon RF transistor
in plastic package SOT-37



Pinouts:
1- Base, 2- Collector, 3-Emitter

Ratings

Symbol	Parameter, unit	Limits
V_{CBO}	Collector- base voltage, V	**20**
V_{CEO}	Collector- emitter voltage, V	**15**
V_{EBO}	Emitter- base voltage, V	**3**
I_C	Collector current, mA	**75**
P_{tot}	Power dissipation, mW	**700**

Characteristics ($T_A = 25°C$)

Symbol	Parameter, unit, test conditions	Limits	
		min	max
f_T	Transition frequency, GHz, I_E=50mA, V_{CB}=10V	**3.2**	
h_{FE}	DC current gain, I_E=50mA, V_{CB}=10V	**50**	
I_{CBO}	Collector cut-off current, nA, I_E= 0mA, V_{CB}=10V		**100**
G_{PS}	Power gain, dB, I_E=50mA, V_{CE}=10V, f=500MHz	**13.0**	
F	Noise figure, dB I_E=50mA, V_{CE}=10V, f=500MHz		**4.0**
C_C	Collector capacitance, pF, V_{CB}=10V, f= 1MHz		**2.0**

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